

ABSTRACT OF THE DISCLOSURE

5 A photosensitive film pattern formed through only one  
photolithography step and having difference in film thickness  
is formed utilizing difference in amount of light emitted to  
the photosensitive film on a film to be etched, and the film  
to be etched is etched two times to form plural patterns therein  
by utilizing the difference in film thickness of the  
photosensitive film pattern, thereby reducing the number of  
10 whole manufacturing process steps. In this case, at the time  
of etching and removing thin photosensitive film out of the  
photosensitive film pattern, the upper layer of thick  
photosensitive film out of the photosensitive film pattern has  
already been modified to a silica film nearly free from being  
15 affected by dry-etching, and therefore, the thick  
photosensitive film can maintain its planar shape nearly equal  
to that of the thick photosensitive film before etching the  
thin photosensitive film. Accordingly, the film to be etched  
is etched to have a pattern nearly equal to designed pattern  
20 by using the silica film as a mask.

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